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A	2016-5				
B	2019-4-20		0 1 2 3 4) 5 6 7 8 9 :	; < =	> ? @
C	2021-10-26	4	A B C D 3 E F G H I J K L :	M N	> ? @

/ Descriptions

SOT-363 O P P 2 Q PNP R S T U V W X

Double silicon PNP transistor in a SOT-363 Plastic Package.

/ Features

Y h_{FE} Z [$V_{CE(sat)}$ X C D \] X

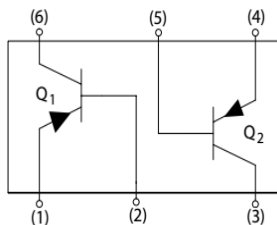
High DC Current Gain, Low Collector to Emitter Saturation Voltage. HF Product.

/ Applications

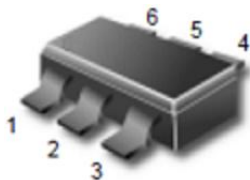
^ _ ` a b c) d e X

General purpose amplifier and switching.

/ Equivalent Circuit



/ Pinning



PIN 1 F 4 f Emitter

PIN 2 F 5 f Base

PIN 3 F 6 f Collector

/ h_{FE} Classifications & Marking

See Marking Instructions.

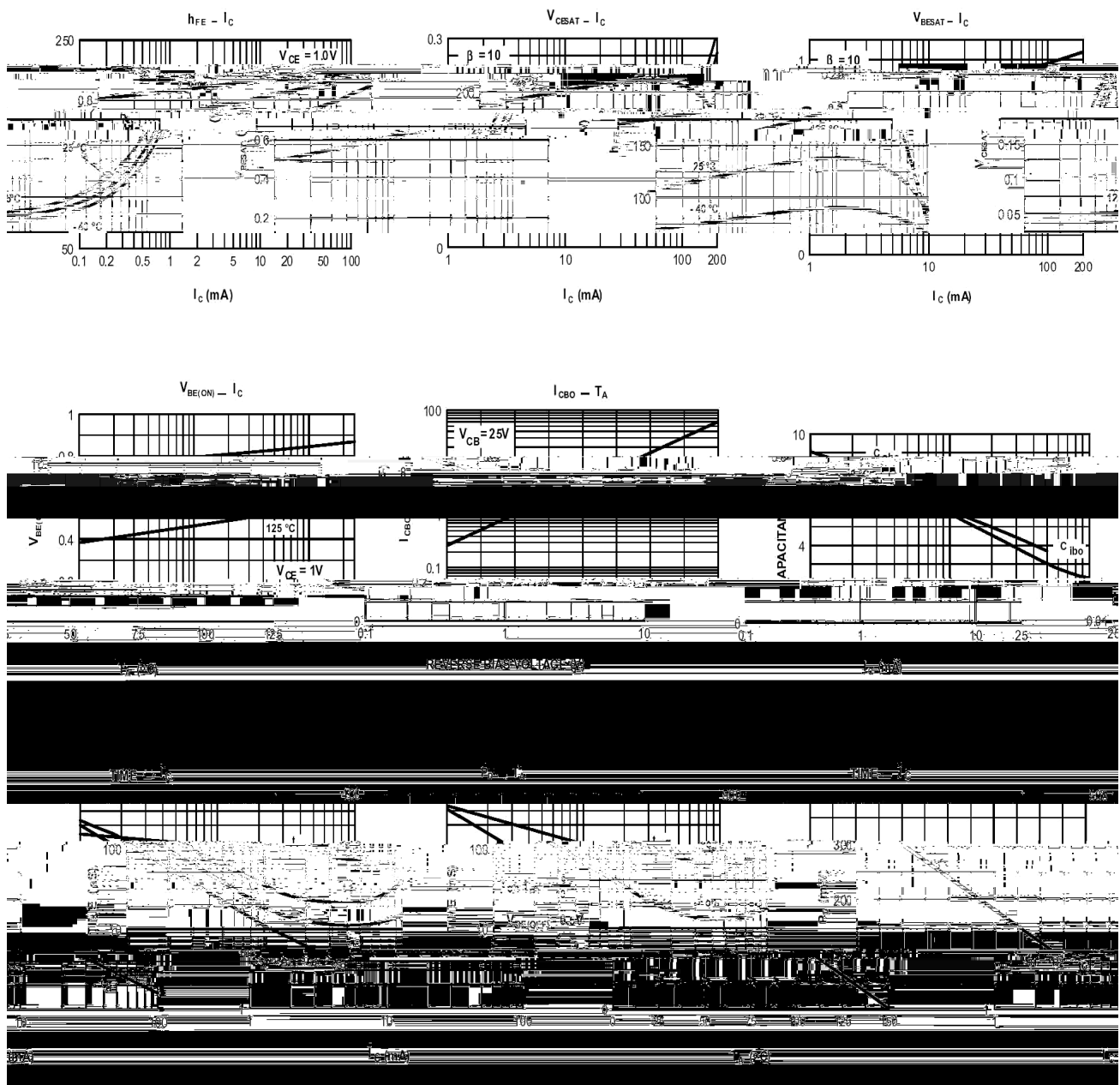
/ Absolute Maximum Ratings(Ta=25)

g h Parameter	i j Symbol	h k Rating	l m Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-200	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

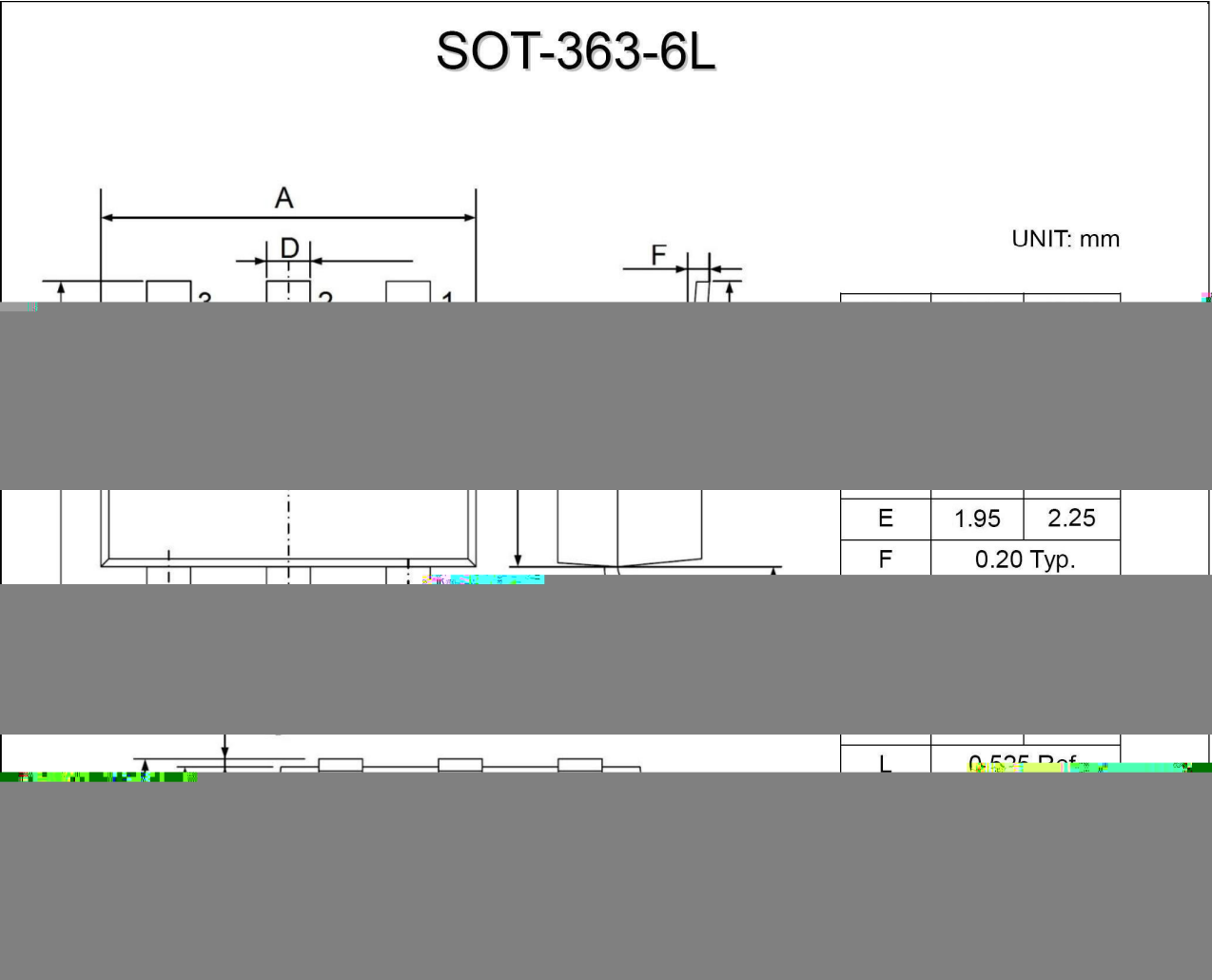
/ Electrical Characteristics(Ta=25)

g h Parameter	i j Symbol	n o p q Test Conditions	r s k Min	t u k Typ	r c k Max	l m Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.05	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3.0V$ $I_C=0$			-0.05	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	30			
	$h_{FE(3)}$	$V_{CE}=-1.0V$ $I_C=-50mA$	60			
	$h_{FE(4)}$	$V_{CE}=-1.0V$ $I_C=-1.0mA$	80			
	$h_{FE(5)}$	$V_{CE}=-1.0V$ $I_C=-0.1mA$	60			
Collector-Emitter Saturation voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$			-0.25	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$	-0.65		-0.85	V
	$V_{BE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.95	V
Transition Frequency	f_T	$V_{CE}=-20V$ $I_C=-10mA$ $f=100MHz$	250			MHz
Output Capacitance	C_{ob}	$V_{CB}=-5.0V$ $f=1.0MHz$			4.5	pF
Storage Time	t_{stg}	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			225	ns
Fall Time	t_f	$V_{CC}=-3.0V$ $I_C=-10mA$ $I_{B1}=-I_{B2}=-1.0mA$			75	ns
Delay Time	t_d	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Rise Time	t_r	$V_{CC}=-3.0V$ $V_{BE}=-0.5V$ $I_C=-10mA$ $I_{B1}=-1.0mA$			35	ns
Input Capacitance	C_{ib}	$V_{EB}=-0.5V$ $f=1.0MHz$			10	pF

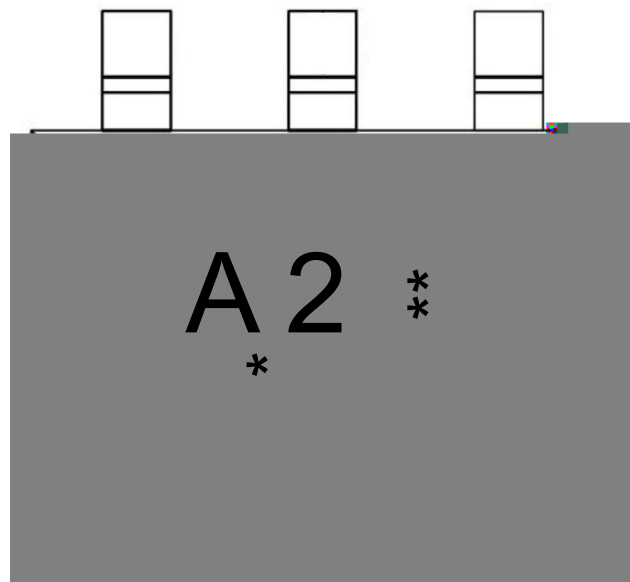
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



v w f

● f x y 1 z {

A2 f x u j | '

***: x } \ ~ j | ' Z i } \ ~ j ¢ £

Note:

● f "1" Pin

A2 f Product Type Code

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

说明：

- 1、预热温度 150 ~ 180℃，时间 60 ~ 90sec;
- 2、峰值温度 245±5℃，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10℃/sec.

Note:

- 1.Preheating:150~180℃, Time:60~90sec.
- 2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度：260±5℃

时间：10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ Packaging SPEC.

卷盘包装 / REEL

Package Type
封装形式

Units 包装数量

Dimens